

ALTERNATIVE TO PTO/SB/08A/B  
(Based on PTO 08-08 version)

Substitute for form 1449/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)			<b>Complete if Known</b>		
			Application Number	10/537,804	
			Filing Date	June 7, 2005	
			First Named Inventor	Robert DWILINSKI	
			Art Unit	1792	
			Examiner Name	F. C. Hiteshew	
			Attorney Docket Number	204552035400	
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	3.	US-6,355,497-B1	03-12-2002	Romano et al.	
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Examiner Initials*	Cite No.	Foreign Patent Document Country Code <sup>2</sup> -Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
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		Art Unit	1792
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		Attorney Docket Number	204552035400

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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T <sup>2</sup>
	50.	Supplementary European Search Report, dated September 23, 2008, European Patent Application No.02788783.5; 3 pages			
	51.	Chinese Office Action, dated July 18, 2008, directed to Chinese Patent Application No. 200580040008.X; 25 pages			✓
	52.	Chinese Office Action, dated December 28, 2007, directed to Chinese Patent Application No. 02802023.5; 8 pages			✓
	53.	Japanese Notification, mailed March 14, 2006, directed to Japanese Patent Application No. 2003-50367; 3 pages			✓
	54.	Japanese Notification of Reason(s) for Refusal, mailed December 16, 2008, directed to Japanese Patent Application No. 2004-505416; 7 pages			✓
	55.	Japanese Notification of Reason(s) for Refusal, mailed January 6, 2009, directed to Japanese Patent Application No. 2004-506101; 7 pages			✓

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		Attorney Docket Number	204552035400
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72.	Penkala, T., (1972). "Zarys Krystalografii (Basics of Crystallography)". PWN, Warszawa: 349	✓

Examiner Signature	/Felisa Hiteshew/	Date Considered	06/05/2009
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<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.